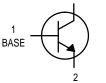
Switching Transistors NPN Silicon

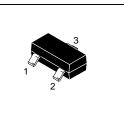
COLLECTOR 3



EMITTER

MAXIMUM RATINGS

			-	
Rating	Symbol	Value	Unit	
Collector-Emitter Voltage	VCEO	15	Vdc	
Collector-Emitter Voltage	VCES	40	Vdc	
Collector-Base Voltage	V _{CBO}	40	Vdc	
Emitter-Base Voltage	V _{EBO}	4.5	Vdc	
Collector Current — Continuous	۱ _C	200	mAdc	



MMBT2369LT1

MMBT2369ALT1*

*Motorola Preferred Device

CASE 318-08, STYLE 6 SOT-23 (TO-236AB)

Max

Тур

Unit

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit	
Total Device Dissipation FR-5 Board ⁽¹⁾	PD	225	mW	
T _A = 25°C Derate above 25°C		1.8	mW/°C	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	°C/W	
Total Device Dissipation Alumina Substrate, ⁽²⁾ T _A = 25°C	PD	300	mW	
Derate above 25°C		2.4	mW/°C	
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	°C/W	
Junction and Storage Temperature	TJ, Tstg	-55 to +150	°C	

DEVICE MARKING

MMBT2369LT1 = M1J; MMBT2369ALT1 = 1JA

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic Symbol Min

OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (3) ($I_C = 10 \text{ mAdc}, I_B = 0$)	V(BR)CEO	15	_	_	Vdc
Collector-Emitter Breakdown Voltage $(I_{C} = 10 \ \mu Adc, V_{BE} = 0)$	V(BR)CES	40	_	_	Vdc
Collector–Base Breakdown Voltage $(I_{C} = 10 \ \mu Adc, I_{E} = 0)$	V(BR)CBO	40	_	_	Vdc
Emitter-Base Breakdown Voltage (I _E = 10 μAdc, I _C = 0)	V(BR)EBO	4.5	_	_	Vdc
Collector Cutoff Current ($V_{CB} = 20$ Vdc, $I_E = 0$) ($V_{CB} = 20$ Vdc, $I_E = 0$, $T_A = 150^{\circ}C$)	ІСВО			0.4 30	μAdc
Collector Cutoff Current ($V_{CE} = 20 \text{ Vdc}, V_{BE} = 0$) MI	MBT2369A	_	_	0.4	μAdc

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.

2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.

3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

Thermal Clad is a trademark of the Bergquist Company.

Preferred devices are Motorola recommended choices for future use and best overall value.



ELECTRICAL CHARACTERISTICS (continued) (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Тур	Мах	Unit
ON CHARACTERISTICS						
$\begin{array}{l} \text{DC Current Gain (3)} \\ (I_{C} = 10 \text{ mAdc}, \text{V}_{CE} = 1.0 \text{ Vdc}) \\ (I_{C} = 10 \text{ mAdc}, \text{V}_{CE} = 1.0 \text{ Vdc}) \\ (I_{C} = 10 \text{ mAdc}, \text{V}_{CE} = 0.35 \text{ Vdc}) \\ (I_{C} = 10 \text{ mAdc}, \text{V}_{CE} = 0.35 \text{ Vdc}, \text{T}_{A} = -55^{\circ}\text{C}) \\ (I_{C} = 30 \text{ mAdc}, \text{V}_{CE} = 0.4 \text{ Vdc}) \\ (I_{C} = 100 \text{ mAdc}, \text{V}_{CE} = 2.0 \text{ Vdc}) \\ (I_{C} = 100 \text{ mAdc}, \text{V}_{CE} = 1.0 \text{ Vdc}) \end{array}$	MMBT2369 MMBT2369A MMBT2369A MMBT2369A MMBT2369A MMBT2369 MMBT2369A	hfe	40 20 30 20 20	 	120 120 — — — —	_
Collector-Emitter Saturation Voltage (3) (I _C = 10 mAdc, I _B = 1.0 mAdc) (I _C = 10 mAdc, I _B = 1.0 mAdc) (I _C = 10 mAdc, I _B = 1.0 mAdc, T _A = +125°C) (I _C = 30 mAdc, I _B = 3.0 mAdc) (I _C = 100 mAdc, I _B = 10 mAdc)	MMBT2369 MMBT2369A MMBT2369A MMBT2369A MMBT2369A	VCE(sat)	 		0.25 0.20 0.30 0.25 0.50	Vdc
Base-Emitter Saturation Voltage (3) ($I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc}$) ($I_C = 10 \text{ mAdc}, I_B = 1.0 \text{ mAdc}, T_A = -55^{\circ}C$) ($I_C = 30 \text{ mAdc}, I_B = 3.0 \text{ mAdc}$) ($I_C = 100 \text{ mAdc}, I_B = 10 \text{ mAdc}$)	MMBT2369A MMBT2369A MMBT2369A MMBT2369A	VBE(sat)	0.7 — —	 	0.85 1.02 1.15 1.60	Vdc
SMALL-SIGNAL CHARACTERISTICS						
Output Capacitance $(V_{CB} = 5.0 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz})$		C _{obo}	_	_	4.0	pF
Small Signal Current Gain (I _C = 10 mAdc, V _{CE} = 10 Vdc, f = 100 MHz)		h _{fe}	5.0	_	_	_
SWITCHING CHARACTERISTICS						
Storage Time ($I_{B1} = I_{B2} = I_C = 10 \text{ mAdc}$)		t _s	_	5.0	13	ns
Turn–On Time (V_{CC} = 3.0 Vdc, I _C = 10 mAdc, I _{B1} = 3.0 mAdc)		ton	_	8.0	12	ns
Turn–Off Time (V _{CC} = 3.0 Vdc, I _C = 10 mAdc, I _{B1} = 3.0 mAdc, I _{B2} =	1.5 mAdc)	^t off	_	10	18	ns

3. Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%.

SWITCHING TIME EQUIVALENT TEST CIRCUITS FOR 2N2369, 2N3227

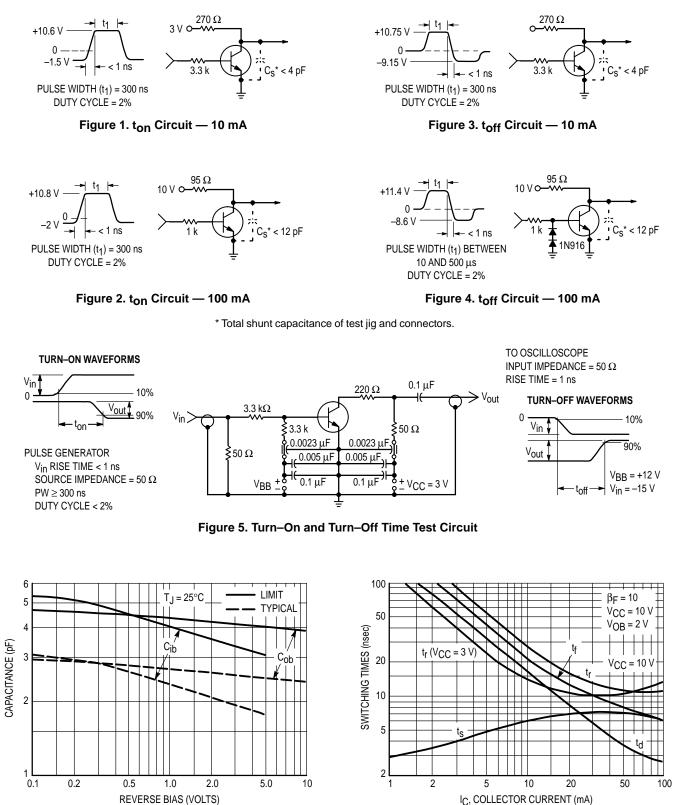


Figure 7. Typical Switching Times

Figure 6. Junction Capacitance Variations

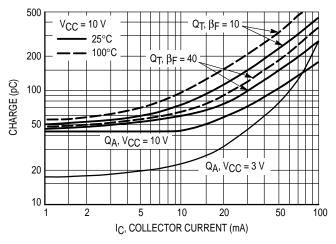
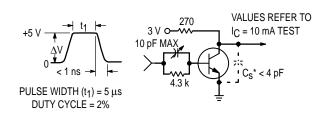


Figure 8. Maximum Charge Data





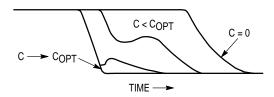


Figure 10. Turn–Off Waveform

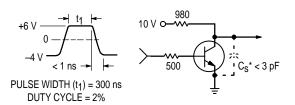


Figure 11. Storage Time Equivalent Test Circuit

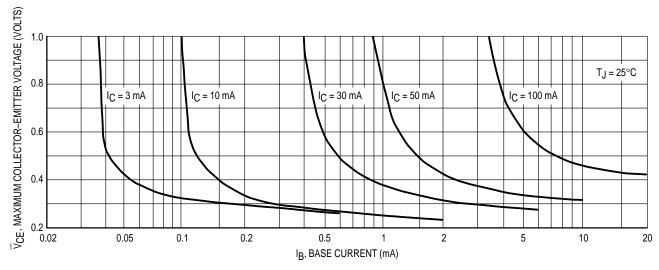
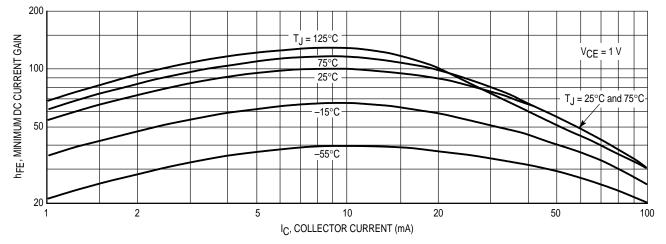


Figure 12. Maximum Collector Saturation Voltage Characteristics





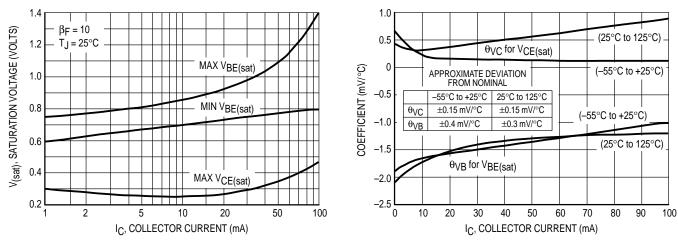


Figure 14. Saturation Voltage Limits

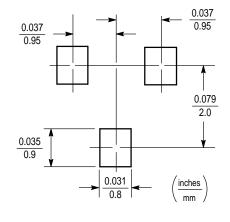
Figure 15. Typical Temperature Coefficients

INFORMATION FOR USING THE SOT-23 SURFACE MOUNT PACKAGE

MINIMUM RECOMMENDED FOOTPRINT FOR SURFACE MOUNTED APPLICATIONS

Surface mount board layout is a critical portion of the total design. The footprint for the semiconductor packages must be the correct size to insure proper solder connection

interface between the board and the package. With the correct pad geometry, the packages will self align when subjected to a solder reflow process.





SOT-23 POWER DISSIPATION

The power dissipation of the SOT–23 is a function of the pad size. This can vary from the minimum pad size for soldering to a pad size given for maximum power dissipation. Power dissipation for a surface mount device is determined by $T_{J(max)}$, the maximum rated junction temperature of the die, $R_{\theta JA}$, the thermal resistance from the device junction to ambient, and the operating temperature, T_A . Using the values provided on the data sheet for the SOT–23 package, PD can be calculated as follows:

$$P_{D} = \frac{T_{J(max)} - T_{A}}{R_{\theta JA}}$$

The values for the equation are found in the maximum ratings table on the data sheet. Substituting these values into the equation for an ambient temperature T_A of 25°C, one can calculate the power dissipation of the device which in this case is 225 milliwatts.

$$P_{D} = \frac{150^{\circ}C - 25^{\circ}C}{556^{\circ}C/W} = 225 \text{ milliwatts}$$

The 556°C/W for the SOT–23 package assumes the use of the recommended footprint on a glass epoxy printed circuit board to achieve a power dissipation of 225 milliwatts. There are other alternatives to achieving higher power dissipation from the SOT–23 package. Another alternative would be to use a ceramic substrate or an aluminum core board such as Thermal Clad[™]. Using a board material such as Thermal Clad, an aluminum core board, the power dissipation can be doubled using the same footprint.

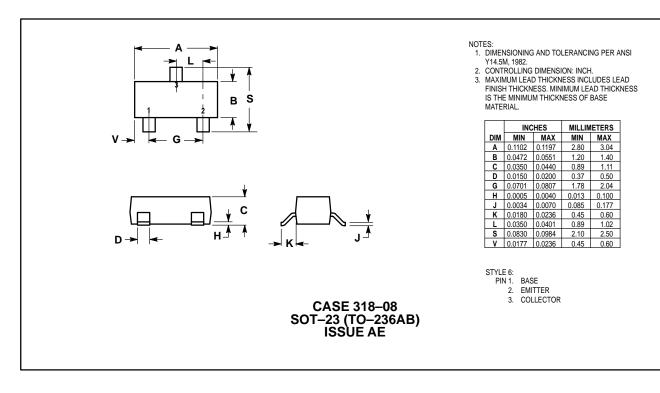
SOLDERING PRECAUTIONS

The melting temperature of solder is higher than the rated temperature of the device. When the entire device is heated to a high temperature, failure to complete soldering within a short time could result in device failure. Therefore, the following items should always be observed in order to minimize the thermal stress to which the devices are subjected.

- Always preheat the device.
- The delta temperature between the preheat and soldering should be 100°C or less.*
- When preheating and soldering, the temperature of the leads and the case must not exceed the maximum temperature ratings as shown on the data sheet. When using infrared heating with the reflow soldering method, the difference shall be a maximum of 10°C.
- The soldering temperature and time shall not exceed 260°C for more than 10 seconds.
- When shifting from preheating to soldering, the maximum temperature gradient shall be 5°C or less.
- After soldering has been completed, the device should be allowed to cool naturally for at least three minutes. Gradual cooling should be used as the use of forced cooling will increase the temperature gradient and result in latent failure due to mechanical stress.
- Mechanical stress or shock should not be applied during cooling.

* Soldering a device without preheating can cause excessive thermal shock and stress which can result in damage to the device.

PACKAGE DIMENSIONS



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